WSJT65R028DR

Super-Junction Power MOSFET

Rev.01 - 16 January 2026 Product data sheet

1. General description

WSJT65R028DR is a high voltage N-channel MOSFET in TO247-4L package, which utilizes the advanced super-junction technology to provide superior FOM $R_{DS(on)}$ * Q_g among silicon based MOSFETs. It is particularly suitable for applications require extreme high efficiency and power density.

RoHS Halogen-Free Lead-Free

2. Features and benefits

- Superior FOM $R_{DS(on)}$ * Q_g
- Extremely low switching loss
- Integrated ultrafast body diode
- 100% avalanche tested

3. Applications

- Suitable for soft switching topologies
- Optimized for phase-shift full bridge(ZVS)
- LLC applications
- EV charger
- Solar

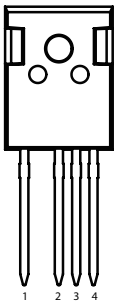
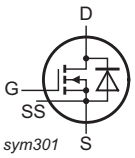
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V_{DS}	drain-source voltage			650			V
V_{GS}	gate-source voltage			±30			V
I_D	continuous drain current	T_C = 25 °C		80			A
P_{tot}	power dissipation	T_C = 25 °C		520			W
T_j	junction temperature			-55 to 150			°C
Symbol	**Parameter**	**Conditions**	**Notes**	**Min**	**Typ**	**Max**	**Unit**
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = 10 V, I_D = 40 A		-	24	28	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 40 A; V_{DS} = 400 V; V_{GS} = 10 V		-	142	-	nC
E_{OSS}	coss stored erergy	V_{GS} = 0 V; V_{DS} = 0 to 400 V		-	21	-	μJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		
2	S	source		
3	SS	source sense		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WSJT65R028DR	TO247-4L	WSJT65R028DRQ	Tube	30	TO247N-4L	17-Dec-2021

7. Marking

Table 4. Marking codes

Type number	Marking codes
WSJT65R028DR	WSJT 65R028DR

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DS}	drain-source voltage			650	V
V_{GS}	gate-source voltage			±30	V
I_D	continuous drain current	T_C = 25 °C		80	A
		T_C = 100 °C		50	A
I_{DM}	pulsed drain current	T_C = 25 °C		320	A
P_{tot}	power dissipation	T_C = 25 °C		520	W
E_{AS}	single pulse drain−to-source avalanche	I_{AS} = 15 A; R_{GS} = 25 Ω; V_{DD} = 50 V; T_j = 25 °C		1125	mJ
E_{AR}	repetitive avalanche energy	I_{AS} = 15 A; R_{GS} = 25 Ω; V_{DD} = 50 V; T_j = 25 °C		2.36	mJ
I_{AS}	avalanche current, single pulse			15	A
dv/dt	MOSFET dv/dt ruggedness			50	V/ns
dv/dt	reverse diode dv/dt			50	V/ns
dI_F/dt	maximum diode commutation speed			750	A/µs
T_{stg}	storage temperature			-55 to 150	°C
T_j	junction temperature			-55 to 150	°C

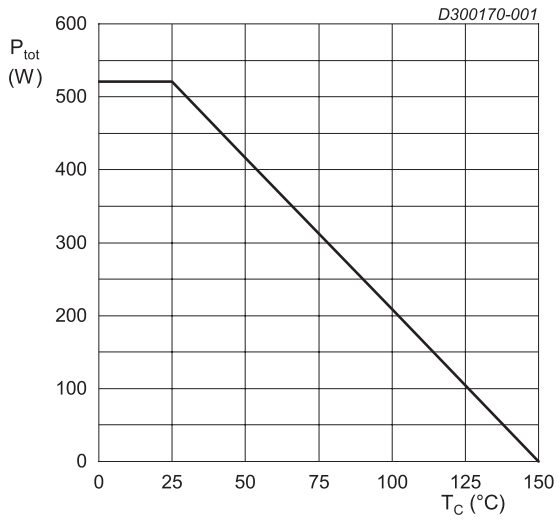


Fig. 1. Total power dissipation as a function of case temperature

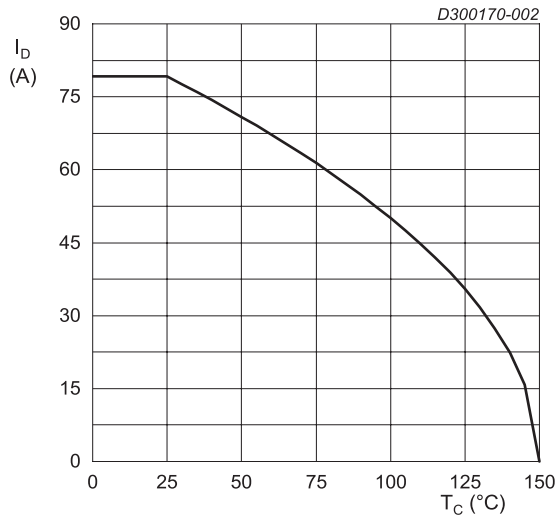


Fig. 2. Continuous Drain Current as a function of case temperature

9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case			-	0.19	0.24	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	45	-	K/W

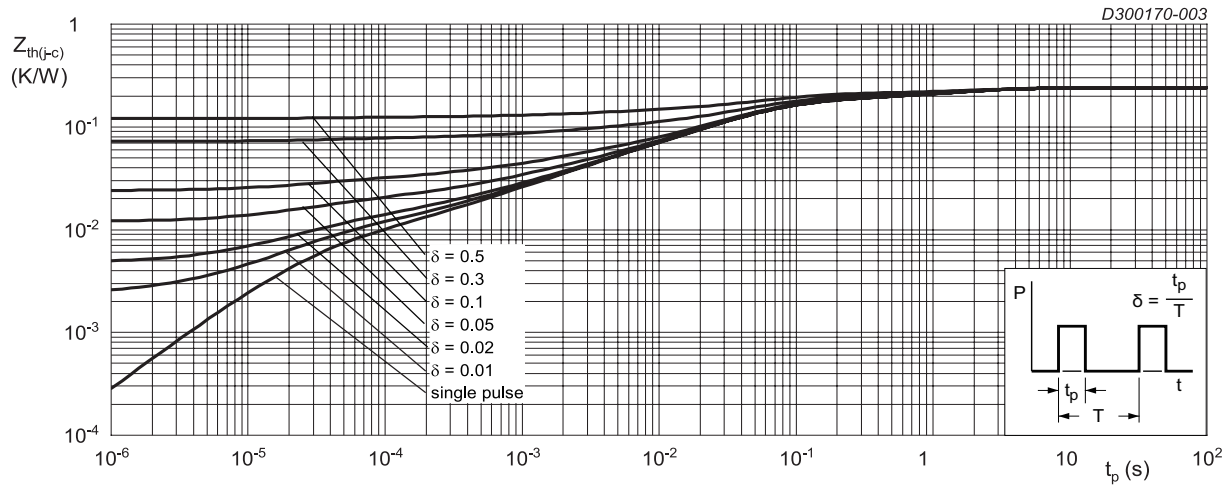


Fig. 3. Transient thermal impedance from junction to case as a function of pulse duration; maximum values

10. Characteristics

Table 7. Characteristics

T_j = 25 °C unless otherwise noted

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 1 mA; V_{GS} = 0 V		650	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS}		3.0	-	5.0	V
I_{DSS}	drain leakage current	V_{DS} = 650 V; V_{GS} = 0 V		-	-	20	µA
		V_{DS} = 650 V; V_{GS} = 0 V; T_j = 125 °C		-	500	-	µA
I_{GSS}	gate leakage current	V_{GS} = ±30 V; V_{DS} = 0 V		-	-	±100	nA
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = 10 V; I_D = 40 A		-	24	28	mΩ
R_G	gate resistance	f = 1 MHz		-	1.0	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 40 A; V_{DS} = 400 V; V_{GS} = 10 V		-	142	-	nC
Q_{GS}	gate-source charge			-	49	-	nC
Q_{GD}	gate-drain charge			-	45	-	nC
C_{iss}	input capacitance	V_{DS} = 400 V; V_{GS} = 0 V; f = 250 KHz		-	8068	-	pF
C_{oss}	output capacitance			-	159	-	pF
C_{rss}	reverse transfer capacitance			-	1.7	-	pF
$C_{o(er)}$	effective output capacitance, energy related	V_{GS} = 0 V; V_{DS} = 0 to 400 V		-	264	-	pF
$C_{o(tr)}$	effective output capacitance, time related			-	1873	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 400 V; V_{GS} = 10 V; R_G = 4 Ω; I_D = 40 A		-	73	-	ns
t_r	rise time			-	14	-	ns
$t_{d(off)}$	turn-off delay time			-	68	-	ns
t_f	fall time			-	2.8	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	V_{GS} = 0 V; I_S = 40 A		-	0.9	1.2	V
I_S	body-diode continuous current	T_C = 25 °C		-	-	80	A
t_{rr}	reverse recovery time	V_R = 400 V; I_F = 40 A; dI_F/dt = 100 A/µs		-	225	-	ns
Q_{rr}	reverse recovered charge			-	2.4	-	µC
I_{rrm}	reverse recovery current			-	20	-	A

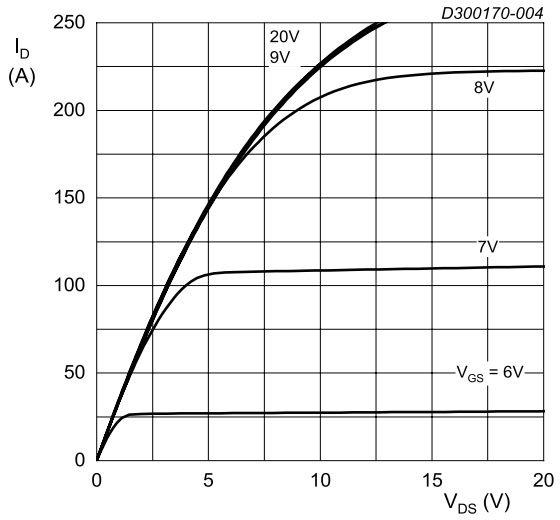
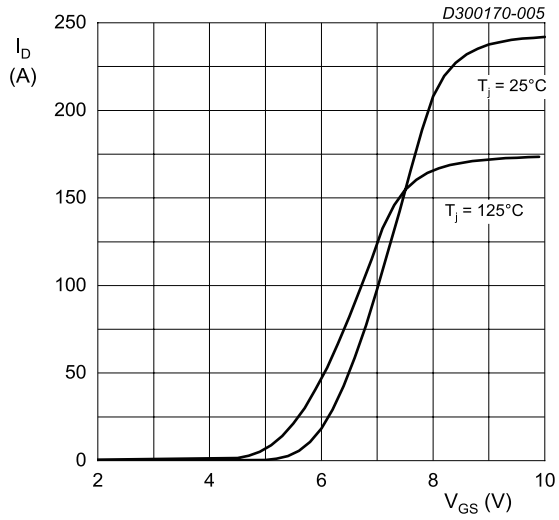
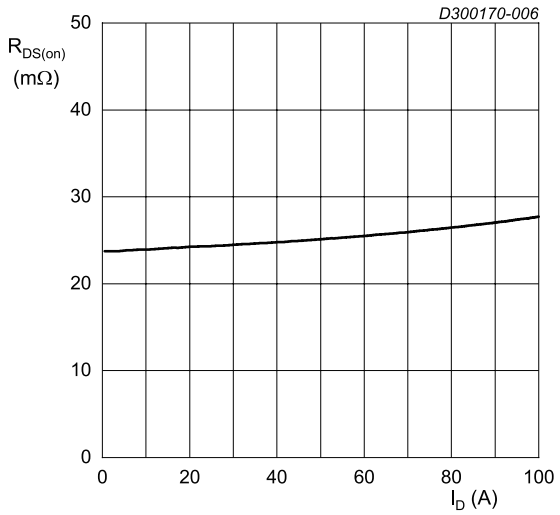


Fig. 4. Drain current as a function of drain-source voltage; typical values



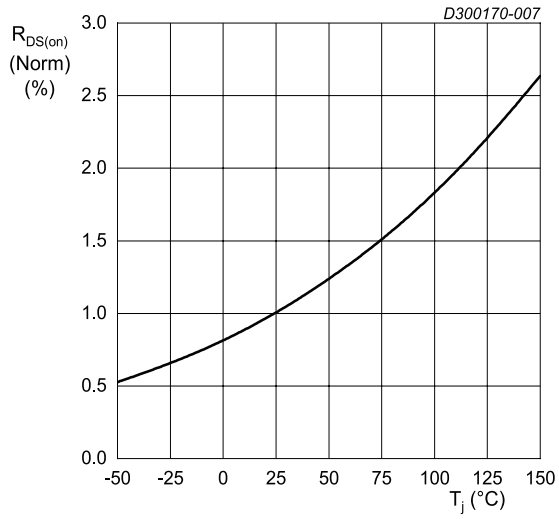
V_{DS} = 20 V

Fig. 5. Drain current as a function of gate-source voltage; typical values



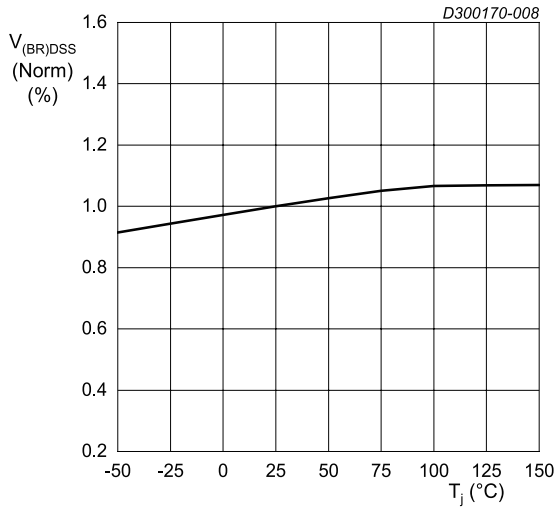
V_{GS} = 10 V

Fig. 6. Drain-source on-state resistance as a function of drain current; typical values



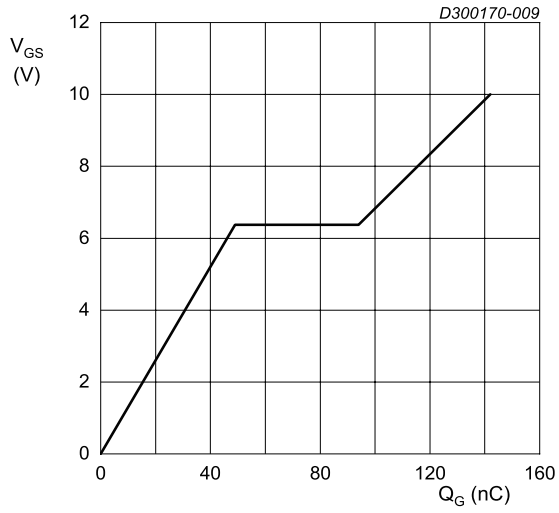
V_{GS} = 10 V; I_D = 40 A

Fig. 7. Normalized drain-source on-state resistance as a function of junction temperature



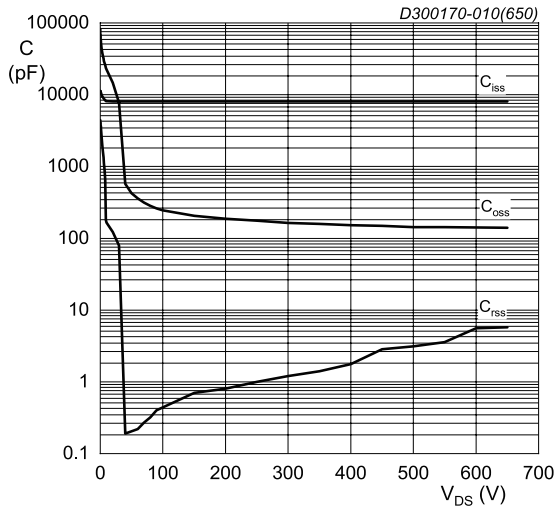
I_D = 10 mA

Fig. 8. Normalized drain-source breakdown voltage as a function of junction temperature



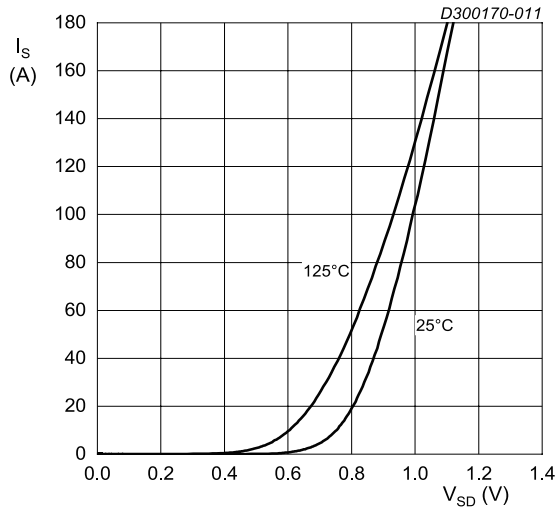
I_D = 40 A; V_{DS} = 400 V

Fig. 9. Gate-source voltage as a function of gate charge; typical values



V_{GS} = 0 V; f = 250 KHz

Fig 10. Capacitances as a function of drain-source voltage; typical values



V_{GS} = 0 V

Fig 11. Source current as a function of source-drain voltage; typical values

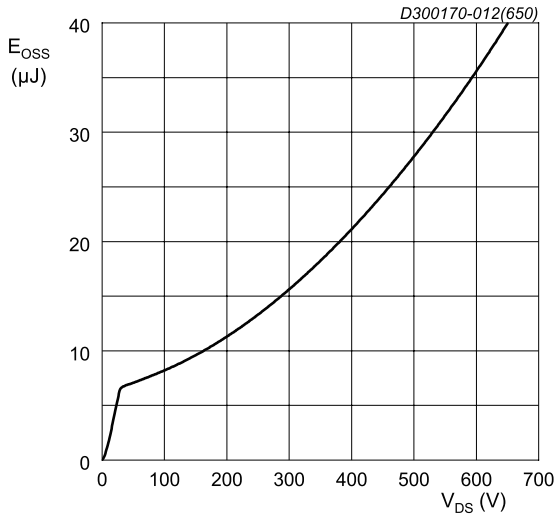
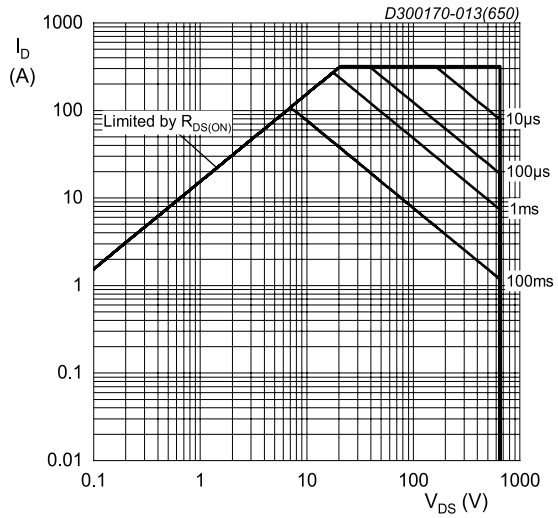


Fig. 12. Output capacitance stored energy as a function of drain-source voltage

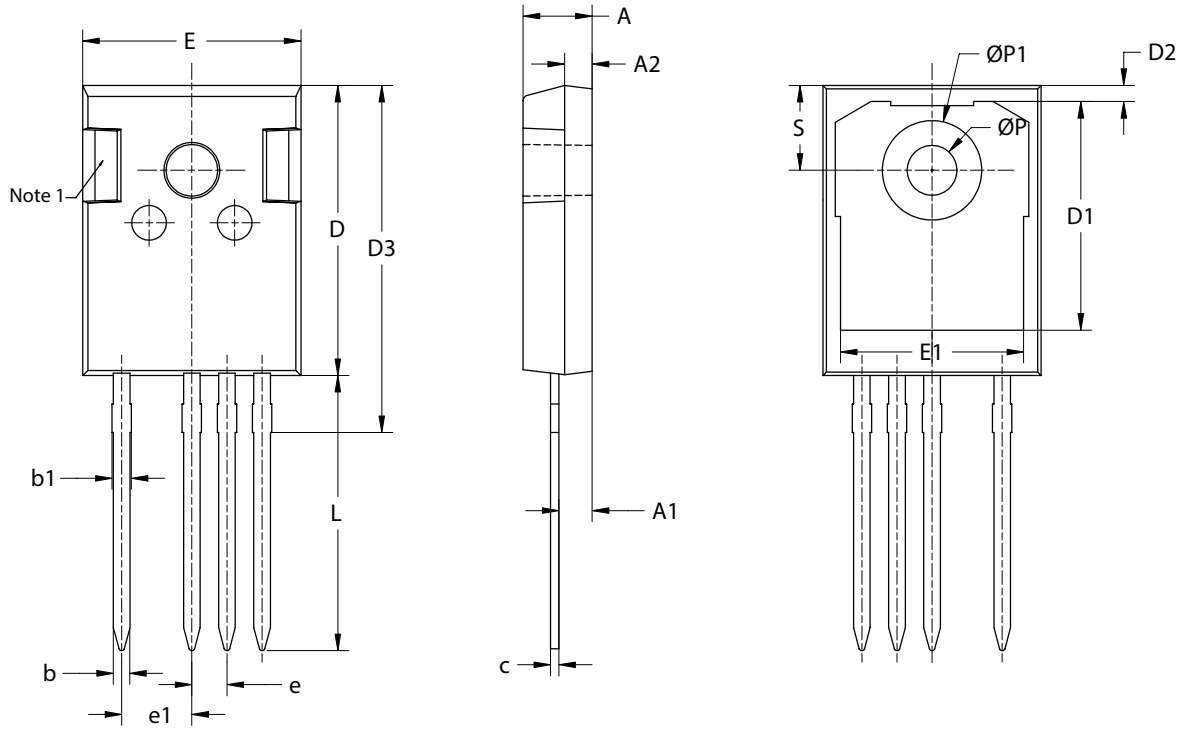


T_C = 25 °C

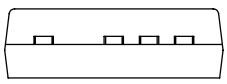
Fig. 13. Safe operating area

11. Package outline

Plastic single-ended through-hole package; heatsink mounted;1 mounting hole; 4 leads TO-247 TO247-4L



TOP VIEW SIDE VIEW BOTTOM VIEW



SIDE VIEW

UNIT		A	A1	A2	b	b1	c	D	D1	D2	D3	E	E1	e	e1	L	P	P1	S
mm	MAX	5.10	2.51	2.10	1.30	1.80	0.70	21.10	16.85	1.35	25.27	15.90	13.50	2.64	5.18	20.10	3.70	(7.40)	(6.15)
	NOM													2.54	5.08				
	MIN	4.90	2.31	1.90	1.10	1.10	0.50	20.90	16.25	1.05	24.97	15.70	13.10	2.44	4.98	19.80	3.50	-	

Note:
1. Metal exposed with Sn plating.
2. All dimensions do not include mold flash & gate remain

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[1] Please consult the most recently issued document before initiating or completing a design.
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13. Contents

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